

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-12. (Canceled)

13. (Currently Amended) The semiconductor device according to claim ~~[[12]]~~ 24, wherein the opposing side surfaces of the first element region oppose each other in a direction of a channel length.

14. (Canceled).

15. (Currently Amended) The semiconductor device according to claim 13, wherein a distance between the first projection and the second projection a length of the recesses in a direction of a channel width is longer than a distance between the first element region and a second element region ~~provided which is~~ separate from the first element region in ~~[[the]]~~ a direction of ~~[[the]]~~ a channel width, and
a distance between the third projection and the fourth projection is longer than the distance between the first element region and the second element region.

16. (Canceled).

17. (Currently Amended) The semiconductor device according to claim ~~[[12]]~~ 24, wherein the element isolation region is formed of a material having a lower thermal expansion coefficient than a material of the first element region.

18. (Currently Amended) The semiconductor device according to claim ~~[[12]]~~ 24, wherein the first element region is formed of Si, and the element isolation region is formed of SiO₂.

19. (Currently Amended) The semiconductor device according to claim ~~[[12]]~~ 24, wherein the semiconductor device is an N-type semiconductor device.

20-23. (Canceled)

24. (Currently Amended) A semiconductor device comprising:

a semiconductor substrate;

a first element region formed in the semiconductor substrate, a gate electrode being provided on the first element region, source and drain regions being formed in the first element region;

first and second projections provided on one of opposing side surfaces of the first element region and made of the same material as the first element region, the first and second region projections being provided on both ends of said one of the side surfaces;

third and fourth projections provided on another one of the opposing side surfaces and made of the same material as the first element region, the third and fourth projections being provided on both ends of said another one of the side surfaces; and

an element isolation region provided around the first element region and the projections.

25. (Canceled).